Fifty Years of Seeing and Experimenting with Single Surface Atoms

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Fifty Years of Seeing Atoms

Beyond imaging atoms, clusters, and defects on a surface, today's microscopes can distinguish elements, monitor their diffusion and redistribution near the surface, and even create designer nanostructures and reactions.

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Democritus (~460 BC)

Leucippus (~5C BC) Epicurus (341-271 BC) Atoms is the fundamental constituent of matters

A Long Journey to See the Invisible : Atoms

Optical Microscope: 9th c. by Arabs & 15th c. to Europe **Compound Optical Microscope: Z. Janssen in 1590** Galileo in 1609 Seeing microorganisms: van Leeuwenhoek in 1674 **Other important contributors: Hooke, Huygens** Limitation: lens aberrations, wave diffraction limit **Resolution:** $\lambda/2 \sim 3000$ Å larger than atoms by ~1000





Ibn Al-Haytham (965-c1040) Optics

Detailed analysis of the eye, coupled with light rays entering the eye gave his optics a very modern twist, influenced Kepler and Descartes.





Galileo

Encarta Encyclopedia, Culver Pictures

Leeuwenhoek



Huygens

He left no portrait of himself

Hooke



Encarta Encyclopedia, Art Resource, NY/Scala

Telescope of Galileo



Compound Optical Microscope of Robert Hooke

Electron Microscope: many recognized the possibility right after de Broglie's matter wave in 1924 **Transmission EM: Knoll & Ruska in 1931 Field Emission Microscope: Müller in 1936 Field Ion Microscope:** Müller in 1951, atom seen in 1955 Scanning TEM: high-Z atoms seen in 1969 by Crewe et al. **Topografiner:** Young in 1972, scan with three orthogonal piezo pieces, operated in field emission regime **Scanning Tunneling Microscope: Binnig, Rohrer in 1982 Atomic Force Microscope: Binnig et al. in 1986**

2005: The Golden Anniversary of Seeing Atoms



Field Emission Microscope 1936, Field Ion Microscope 1951, Atom-Probe FIM 1967



1964

~1972







Topografiner Young '71 Field emission mode Optical Grating STM Binnig & Rohrer et al. '83 Vaccum tunneling mode Si(111)-7x7 surface

AFM Binnig et al. '86 Contact mode Al₂O₃ ceramic



10/15/86 just after the announcement of the Nobel Prize for G. Binnig & H. Rohrer With C. Quate, M. Aono, W. Goodman and K. Sattler in Honolulu, Hawaii in ~2000



STM & TEM Images of Si(111)-7x7 Surface & Ag Nano Crystals Grown on Multiwall Carbon Nanotube

FIM Image of **Gold** and a Model for an fcc Tip





Müller's first FIM (1951)

1960s to early 1970s: Instrumentations & Basic principle



Field evaporation: charge states & rate vs. field

Field adsorption: metal helide ion formation, Langmuir adsorption isotherm

Field ionization: I-V characteristics & ion energy distribution

Field Ion Energy Distributions Field ionization occurs in

spatial disks of ~0.2Å



Southon & Brandon, Phil Mag '63



'n

From step edge atoms: Tsong & Müller, JCP '64



From a flat surface: Jason et al. H⁺, H₂⁺ & H₃⁺ ions, JCP '67



|(in)

Langmuir Adsorption-Isotherm for Field Adsorption

$$p(\infty) = \left[1 + \frac{\nu_0 C T^j}{p_g F_0^i} \exp\left(-\frac{H}{kT}\right)\right]^{-1}.$$
 (2.56)

This equation for i = j = 1 was originally derived by Tsong & Müller. It was recognized by Rendulic¹²¹ to be a form of Langmuir isotherm specific to field adsorption. The probability of adsorption on a surface atom is of course equivalent to the degree of coverage of the surface if all the atoms in the surface have the same field strength. In the present equation, the field enhancement as well as the time-dependent behavior have been taken into account. For analyzing experimental data, eq. (2.56) is best rearranged in the following form:¹¹⁵

$$\ln\left[\left(\frac{1}{p}-1\right)/T^{j}\right] = \ln\left(\frac{\nu_{0}C}{p_{g}F_{0}^{j}}\right) - \frac{H}{kT}.$$
(2.57)



Metal Helide Formation & Field Dissociation



Non-Destructive Chemical Mapping of Surfaces of Ordered Alloys: Images of Ordered Pt₃Co & PtCo



Tsong & Müller, Appl. Phys. Lett. 9 (1966) 7 etc. STM image of PtRh P. Varga et al.

ToF Atom-Probe FIM: flight time focusing method High voltage pulse operated AP: A very large ion energy spread





Proto type ToF AP Müller, Panitz & McLane, RSI '68 **Porschenrieder type ToF AP**

Müller & Krisnaswamy, RSI '72

Atomic Layer by Layer Nano Surface Analysis in Alloy Segregation Ni-5%Cu, Ng & Tsong PRL '79





Pulsed Laser Time-of-Flight Atom-Probe FIM (82-90) Single Atom Chemical & Energy Analysis for Poor Conducting Materials



Local electrode: 1) For reducing the voltage to improve mass resolution. 2) For accurate positioning of the tip. 3) For creating a field free flight path.
 T. T. Tsong, Atom-Probe Field Ion Microscopy, Cambridge Univ. Press (90)

Tsong, IP AS



Nano-Analysis with 3D Atom-Probe

Impurity segregation to line dislocation core



Blavette et al. Science '93

Cerezo & Smith Oxford Univ. Kelly et al.: Imago

3D ToF Atom-Probe Field Ion Microscope

Single Atom Experiments:

1. How atoms diffuse and interact on the surface ?

2. How from such interaction atoms grow into a cluster or a nano island and what are their structures ?

3. What are the properties of a surface nano structure ?

Atom & Molecular Dynamics, or Diffusion at Surfaces

Macroscopic Description

Fick's law of diffusion

 $\vec{J} = -\vec{D}\nabla c + c(\vec{\upsilon})_{\vec{F}}$

Microscopic Description $U(\vec{r} + \vec{\rho}_n) = U(\vec{r})$

 $\vec{\rho}_n$: Surface lattice vector

The Question is:

How D & <n> are related to one another?

 $\overline{n} = v_0 \exp(-\Delta G/kT)$ Average # of jumps/unit time $\Delta G = E_d - T\Delta S$ ΔG : Gibb's free energy ΔS : Entropy

 $\overline{N} = \overline{n}\tau = \tau v \exp(-E_d/kT)$ where $v = v_0 \exp(\Delta S/k)$



Atomic View of Surface Self-Diffusion: Tungsten on Tungsten*†

GERT EHRLICH AND F. G. HUDDA

General Electric Research and Development Center, Schenectady, New York (Received 30 August 1965)

Surface diffusion of tungsten adatoms on several smooth, low-index planes of the tungsten lattice has for the first time been followed by direct observation of individual atoms in the field-ion microscope. Contrary to expectation, the mobility at room temperature is found to increase in the order $(211) > (321) \sim (110) >$ $(310) \sim (111)$. Migrating atoms are reflected at the boundaries of the (110), (211), and (321) planes; on the latter two, motion along atomic rows is favored over diffusion across lattice steps. From quantitative determinations of the rate of change of the mean-square displacement, diffusion coefficients are obtained as follows: (110), $D=3\times10^{-4}$ exp $(-22\ 000/RT)$ cm³/sec; (321), 1×10^{-3} exp $(-20\ 000/RT)$; (211), 2×10^{-7} exp $(-13\ 000/RT)$. Differences in diffusion on the (211) and (321), planes of very similar structure, suggest a weakening of interatomic forces at lattice edges.

PHYSICAL REVIEW B

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Direct Observation of Interactions between Individual Atoms on Tungsten Surfaces*

Tien Tzou Tsong

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Using the field ion microscope (FIM), it is possible to investigate the interactions between individual atoms on metal surfaces. The number of atoms participating in an experiment can be specified and controlled by successive depositions or field evaporations. It is found that the interaction potential between two atoms depends on the substrate surface structure. In agreement with other investigators, the binding energy is found to be not pairwise additive. The interatomic potential between two Re atoms on W (110) planes shows at least two minima and a maximum, suggesting an oscillatory structure similar to the well-known Friedel oscillation. Surface migration as well as structures of clusters with less than six atoms is also investigated. It is found that the equilibrium structures of the clusters depend very sensitively on surface temperature. It is also found that potential traps of ~ 0.14 eV exist on crystal planes which otherwise appear to be perfectly regular in the FIM images.



Tracing the movements of an atom using **FIM** Tsong PRB '72



surface channel. Each jumping step is 2.74 Å, and the

channel has a total of 17 steps.



FIG. 2. Two-dimensional random walks of a Re atom on a W (110) plane. The vectors connecting two successive positions of the Re atom are displacement vectors rather than diffusion paths. The dark dotted position is where a surface-potential trap is located.



FIG. 5. A map for the three Re atoms shown in Fig. 4. Atoms A and B migrated together until B fell into a potential trap. B started to move again only when the heating temperature was raised to 332 K.



Commemoration of the 100th Anniversary of Einstein's Miraculous Year 1905

Einstein Relation in Random Walk



Atomic-Exchange diffusion mechanism: Ir/Ir(001)



Tracking the movement of one surface atom

Chen & Tsong, PRL' 90, Nature' 91 Kellogg & Feibelman, PRL'90

DAS Model Si(111)-7x7

O₂/Si(111)-7x7: 300 C, 2V, 100 pA



Tsong, IP AS



Site to Site	$\mathbf{E}_{\mathbf{d}}$	$Log\{\nu_0(Hz)\}$
FE to FE	$\textbf{2.04} \pm \textbf{0.04}$	15.0 ± 0.3
FE to FC	$\textbf{2.29} \pm \textbf{0.06}$	16.2 ± 0.5
FC to FE	$\textbf{2.13} \pm \textbf{0.11}$	15.6 ± 1.0
UE to UE	$\boldsymbol{2.16\pm0.04}$	15.9 ± 0.3
UE to UC	$\boldsymbol{2.01 \pm 0.10}$	14.6 ± 0.8
UC to UE	1.96 ± 0.13	14.1 ± 1.1
Intermediate State Hopping		
$\mathbf{B_i}$ to $\mathbf{I_i}^*$	$\boldsymbol{1.83 \pm 0.04}$	13.0 ± 0.4
I _i * to B _i	$\boldsymbol{1.63\pm0.10}$	13.2 ± 0.9
$\mathbf{I_i^*}$ to $\mathbf{I_f^*}$	2.03 ± 0.10	16.1 ± 0.9
2	0 0	0 •

- 1. Site and path specific diffusion parameters
- 2. Diffusion mechanisms: Tumbling mechanism
- 3. Self-catalyzed oxidation





Bottom-up approach: controlled growth of atom-clusters and observing their diffusion-interaction, Hopping Diffusion



Si Magic Nanoclusters Surface Molecule-Like (~12 atoms) The Basic Unit for Mass transport





450 °C

Hwang, Ho & Tsong PRL <u>83</u>, 120 (1999); Ho, Hwang & Tsong PRL <u>84</u>, 5792 (2000)

Dynamic detachment & attachment of Si magic clusters at step edges

Tsong, IP AS

Dynamics of Si Magic Clusters (Surface Molecule-Like) on Si(111)-7x7 at 450 °C Atomic jumps occur in ps, microscopy images are time lapse-images



Electronic Effects on Adsorbate Interactions On Metal Surfaces

Theoretical:

T. L. Einstein & J. R. Schrieffer (73); K. H. Lau & W. Kohn (78)

K. A. Fichthorn & M. Scheffler (00), and many more

Experimental:

FIM: Mostly on W(110) surface Tsong (72, 73), Casanova & Tsong: (80, 81): Pre-PC image digitizer Watanabe & Ehrlich: (89, 91, 92): PC image digitizer available STM: Cu(111) surface, quasi 2D system J. Repp et al. (00) (Rieder) N. Knorr et al. (02) (Brune) Silly et al. (03) (Schneider) **Basic Features:** pair interaction vs. potential of mean force 1. Weak 2. Long range **3.** Oscillatory **Review:** T. T. Tsong, Rep. Prog. Phys. 51 (99) 759 Before STM Studies M. L. Merrick, W-W. Luo and K. A. Fichthorn, Prog. Surf. Sci. 72 (03) 117. Adatom-Adatom Interaction in 1-D: Pd-Pd on W(112)

(a) In same channel
(b) In 1st nn channels
(c) In 2nd nn channels
(d) In 3rd nn channels
X: lateral separation

In the same channel: $E_d(Pd) = 0.32 \pm 0.02 \text{ eV}$ $E_d(Pd_2) = 0.59 \pm 0.05 \text{ eV}$ $E_b(Pd) = 0.61 \pm 0.03 \text{ eV}$

Fu et al. '03







Pd-Pd nnchannel interaction, data taken at 248 K

Best fit curve: cos(2k_FR)/(2k_FR)ⁿ for n=1

 $k_{\rm F} = 0.3 \text{ Å}^{-1}$

Tsong & Casanova, PRL '82





Silly & Schneider et al. PRL '04



Correlation between Adatomadatom interactions & Adlayer structure

Si on W(110)

> Ce on Ag(111)



A Mesoscopic Quantum System: Pb Nanoislands on Si(111) Size Dependence of a Low T Phase Transition of 2D Nano-Islands Pb(1x1) (a brief heating to 400 °C) \leftrightarrow Pb($\sqrt{7}x\sqrt{3}$) on Si(111)-7x7



300 K, red bar = 5 nm, blue bar = 1 nm 190 K, T_t is lower for smaller domains

Landau-Lifshitz: continuous phase transition if low T phase is a subgroup of high T phase, thus temporal & spatial fluctuations can be obseerved.



Hwang et al. (PRL '04)

Finite Size Effect of T_t **There is no well defined transition temperature for finite size nano islands in a structure "phase transition" !**

Finite 2D nano islands on infinite substrate: Weak coupling between islands and substrate

Analysis based on Ising Model (v=1) & 3-State Potts Model (v = 0.83).

Electron Wave Interference Pattern by Impurity Atoms

Atomic Structure Modulation Around Adsorbed H-Atoms





Eigler et al. Nature '91 Su et. al.: Cu(111) H/Pb/Si(111), Hwang & Chang et al. PRL '04

Electronic Morié Pattern of Pb-Si Interfaces (IC Phase) of **Type I & Type II Quantum Islands**



0 0 0 0 0 0 0 0

õ Ő,

o o

• outer layer Si

○ Pb atom

0 0 0 0 0 0 0 0 0 0 0 0

000000000000000000

second layer Si T4 site

00

0 0 0 0

• T1 site

• H3 site

Ŏ.

0.0.0

0 0 0

0 0 0

W-B Jian et al., **PRL 03**



2

Electronic Moriè Pattern as Template: Ag nanopucks (one-layer thick) on quantum Pb islands of 3-layer thick





Chemical Potential Gradient Induced Directional Walk:

Field gradient induced directional random walk

CP gradient can be produced by interactions, conc. & thermal grad.

Non-equilibrium thermodynamics: kinetic effect!

Directional Walk of W on W(112) Produced by Chemical Potential Gradient (Field Gradient)



Tsong, Walko, Kellogg, Wang '72, '75 '82



Some Other Methods of Atomic Manipulation Tsong PRB '91

- **1. Field Gradient Induced Diffusion:** Directional walk. Neck formation.
- **2. Field Evaporation:** Atom transfer between tip & sample



Neck Formation



Manipulation in nanoscale Thermally stable at 300 K



Neck Formation (700 x 1000 nm)

Field Evaporation (70 x 100 nm)

CPG (surface energy diff.) induced thermally & chemically stable & reformable Atom Perfect nm-size Pyramidal Tip



T. Madey et al.: Formation of pyramids by two comp. systems Fu et al. PRB '01; Kuo et al. Nano Lett. '04

 STM chemical mapping
 Coherent electron beam for electron holography
 Point ion source appls.



Atom perfect & chemically inert Pd-covered W(111)-base pyramid. Thermally stable up to ~1000 K, h ~ 1.4 nm

Tsong, IP AS



Fowler-Nordheim Plots



Field emission: extension angle ~ 6° Field ionization: extension angle ~ 0.5° Rokuta & Oshima et al. '05 Kuo & Hwang et al. NANO Lett. '04



Kuo et al. '05

Possible use in Focused Ion Beam Source



Electronic Density of States Mapping of a Surface Using a Thermally & Chemically Stable Tip of Known Apex Atom can Provide a Chemical Map of Surface Atoms



 $I \propto \int_{0}^{eV} \rho_t (E_F - \varepsilon) \rho_S (E_F - eV + \varepsilon) T(d, eV) d\varepsilon \qquad \text{Tersoff \& Hamann '83}$

If ρ_t is a δ -function, or *T*(*d*,*e* ΔV) are nearly constant:

$$\frac{dI}{dV} \propto \rho_{S} \left(E_{F} - eV \right)$$

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Thanks for Your Listening! **Fifty Years of Seeing Atoms** March 2006 Physics Today 31 **Japanese Translation: Parity**: October 2006 issue http://www.sinica.edu.tw/~tsongtt/